

# **PSMN017-80PS**

## N-channel 80 V 17 m $\Omega$ standard level MOSFET in TO220

Rev. 3 — 27 September 2011

**Product data sheet** 

## 1. Product profile

## 1.1 General description

Standard level N-channel MOSFET in TO220 package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

## 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

## 1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

#### 1.4 Quick reference data

Table 1. Quick reference data

Parameter	Conditions	Min	Тур	Max	Unit
drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$	-	-	80	V
drain current	$T_{mb}$ = 25 °C; $V_{GS}$ = 10 V; see <u>Figure 1</u>	-	-	50	Α
total power dissipation	T <sub>mb</sub> = 25 °C; see Figure 2	-	-	103	W
junction temperature		-55	-	175	°C
aracteristics					
drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A};$ $T_j = 100 \text{ °C}; \text{ see } \frac{\text{Figure 12}}{}$	-	15.2	29	mΩ
	$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 13}{}$	-	13.7	17	mΩ
characteristics					
gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$	-	6	-	nC
total gate charge	V <sub>DS</sub> = 40 V; see <u>Figure 14;</u> see <u>Figure 15</u>	-	26	-	nC
Avalanche ruggedness					
non-repetitive drain-source avalanche energy	$V_{GS} = 10 \text{ V; } T_{j(init)} = 25 \text{ °C;}$ $I_D = 50 \text{ A; } V_{sup} \le 80 \text{ V;}$ $R_{GS} = 50 \text{ \Omega; unclamped}$	-	-	55	mJ
	drain-source voltage drain current  total power dissipation junction temperature aracteristics drain-source on-state resistance  characteristics gate-drain charge total gate charge  ne ruggedness non-repetitive drain-source	$\begin{array}{lll} \text{drain-source voltage} & T_{j} \geq 25 \ ^{\circ}\text{C}; \ T_{j} \leq 175 \ ^{\circ}\text{C} \\ \\ \text{drain current} & T_{mb} = 25 \ ^{\circ}\text{C}; \ V_{GS} = 10 \ V; \\ \text{see} \ \frac{\text{Figure 1}}{\text{Igure 1}} \\ \\ \text{total power dissipation} & T_{mb} = 25 \ ^{\circ}\text{C}; \ \text{see} \ \frac{\text{Figure 2}}{\text{Igure 2}} \\ \\ \text{junction temperature} \\ \\ \text{aracteristics} \\ \\ \text{drain-source on-state} & V_{GS} = 10 \ V; \ I_{D} = 10 \ A; \\ \\ T_{j} = 100 \ ^{\circ}\text{C}; \ \text{see} \ \frac{\text{Figure 12}}{\text{Igure 12}} \\ \\ V_{GS} = 10 \ V; \ I_{D} = 10 \ A; \\ \\ T_{j} = 25 \ ^{\circ}\text{C}; \ \text{see} \ \frac{\text{Figure 13}}{\text{Igure 14}} \\ \\ \text{characteristics} \\ \\ \text{gate-drain charge} & V_{GS} = 10 \ V; \ I_{D} = 25 \ A; \\ \\ \text{total gate charge} & V_{DS} = 40 \ V; \ \text{see} \ \frac{\text{Figure 14}}{\text{see} \ \text{Figure 15}} \\ \\ \text{non-repetitive drain-source} \\ \text{avalanche energy} & V_{GS} = 10 \ V; \ T_{j(\text{init})} = 25 \ ^{\circ}\text{C}; \\ \\ I_{D} = 50 \ A; \ V_{\text{sup}} \leq 80 \ V; \\ \\ \end{array}$	$\begin{array}{llllllllllllllllllllllllllllllllllll$	$\begin{array}{llllllllllllllllllllllllllllllllllll$	$\begin{array}{llllllllllllllllllllllllllllllllllll$



## 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain	mb	D
3	S	source		
mb	D	mounting base; connected to drain	1 2 3	mbb076 S
			SOT78 (TO-220AB)	

## 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN017-80PS	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

## 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	80	V
$V_{DGR}$	drain-gate voltage	$T_j \ge 25$ °C; $T_j \le 175$ °C; $R_{GS} = 20$ kΩ	-	80	V
$V_{GS}$	gate-source voltage		-20	20	V
I <sub>D</sub>	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 100 ^{\circ}\text{C}; \text{see } \underline{\text{Figure 1}}$	-	35	Α
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; see <u>Figure 1</u>	-	50	Α
$I_{DM}$	peak drain current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 \text{ °C}$ ; see <u>Figure 3</u>	-	200	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	103	W
T <sub>stg</sub>	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-drain	n diode				
Is	source current	T <sub>mb</sub> = 25 °C	-	50	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$	-	200	Α
Avalanche r	uggedness				
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 50 A; $V_{sup} \le$ 80 V; $R_{GS}$ = 50 $\Omega$ ; unclamped	-	55	mJ

PSMN017-80PS

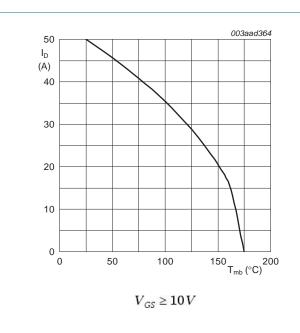


Fig 1. Continuous drain current as a function of mounting base temperature

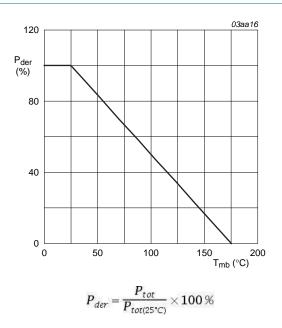
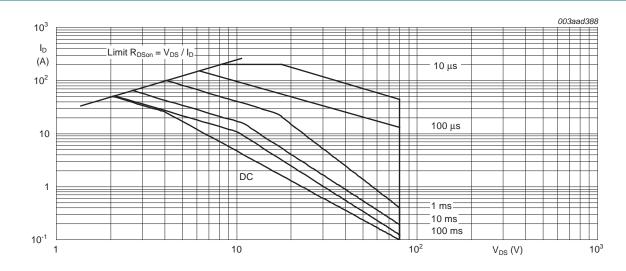


Fig 2. Normalized total power dissipation as a function of mounting base temperature



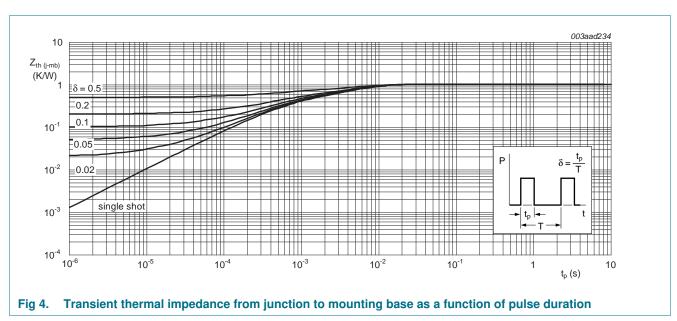
 $V_{\it GS} \geq 10\,V \label{eq:VGS}$  (1) Capped at 100 A due to package.

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

## 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	1	1.5	K/W



## 6. Characteristics

Table 6. Characteristics

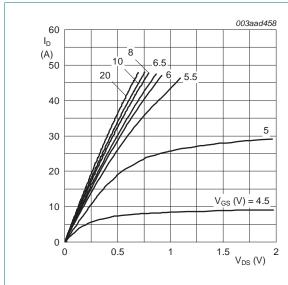
Tested to JEDEC standards where applicable.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	73	-	-	V
	voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	80	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}$ ; $V_{DS} = V_{GS}$ ; $T_j = 175 \text{ °C}$ ; see Figure 10; see Figure 11	1	-	-	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = -55$ °C; see Figure 10; see Figure 11	-	-	4.8	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 25$ °C; see <u>Figure 10</u> ; see <u>Figure 11</u>	2	3	4	V
DSS	drain leakage current	$V_{DS} = 80 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.3	2	μΑ
		$V_{DS} = 80 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ °C}$	-	-	50	μΑ
GSS	gate leakage current	$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nΑ
		$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nΑ
R <sub>DSon</sub> drain-source on-state resistance		$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 175 \text{ °C};$ see Figure 12	-	32.64	40.8	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 100 \text{ °C};$ see Figure 12	-	15.2	29	mΩ
	$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 25 \text{ °C};$ see Figure 13	-	13.7	17	mΩ	
$R_{G}$	internal gate resistance (AC)	f = 1 MHz	-	1	-	Ω
Dynamic ch	aracteristics					
$Q_{G(tot)}$	total gate charge	$I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V$	-	22	-	nC
		$I_D = 25 \text{ A}; V_{DS} = 40 \text{ V}; V_{GS} = 10 \text{ V}; \text{see}$	-	26	-	nC
Q <sub>GS</sub>	gate-source charge	Figure 14; see Figure 15	-	7.7	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source charge		-	4.6	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge		-	3	-	nC
$Q_{GD}$	gate-drain charge		-	6	-	nC
/ <sub>GS(pl)</sub>	gate-source plateau voltage	$I_D = 25 \text{ A}; V_{DS} = 40 \text{ V}; \text{see } \frac{\text{Figure 15}}{}$	-	4.7	-	V
Siss	input capacitance	$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	1573	-	pF
oss	output capacitance	T <sub>j</sub> = 25 °C; see <u>Figure 16</u>	-	154	-	pF
rss	reverse transfer capacitance		-	88	-	pF
d(on)	turn-on delay time	$V_{DS} = 40 \text{ V}; R_L = 1.6 \Omega; V_{GS} = 10 \text{ V};$	-	14	-	ns
	rise time	$R_{G(ext)} = 4.7 \Omega$	-	12	-	ns
d(off)	turn-off delay time		-	27	-	ns
f	fall time		-	8	-	ns

 Table 6.
 Characteristics ...continued

Tested to JEDEC standards where applicable.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-drain	n diode					
V <sub>SD</sub>	source-drain voltage	$I_S$ = 10 A; $V_{GS}$ = 0 V; $T_j$ = 25 °C; see <u>Figure 17</u>	-	0.79	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 40 \text{ A}; dI_S/dt = 100 \text{ A/}\mu\text{s};$	-	41	-	ns
Q <sub>r</sub>	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 40 \text{ V}$	-	55	-	nC



 $T_j = 25 \,^{\circ}C; t_p = 300 \,\mu s$ 

Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

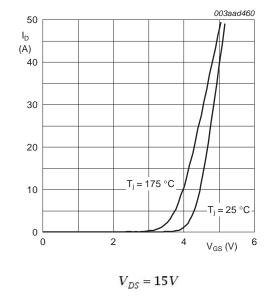


Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values

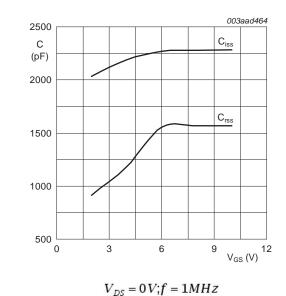
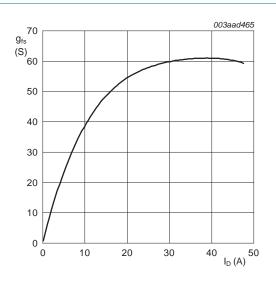


Fig 7. Input and reverse transfer capacitances as a function of gate-source voltage; typical values



 $T_j = 25 \,^{\circ}C; V_{DS} = 15 \, V$ 

Fig 8. Forward transconductance as a function of drain current; typical values

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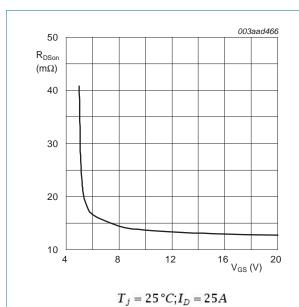
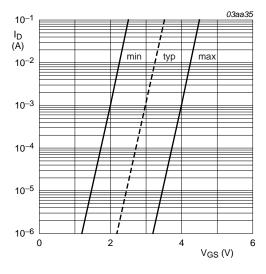


Fig 9. Drain-source on-state resistance as a function

of gate-source voltage; typical values



 $T_j = 25 \,^{\circ}C; V_{DS} = 5V$ 

Fig 10. Sub-threshold drain current as a function of gate-source voltage

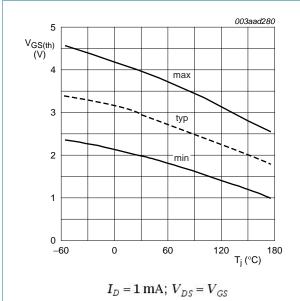


Fig 11. Gate-source threshold voltage as a function of junction temperature

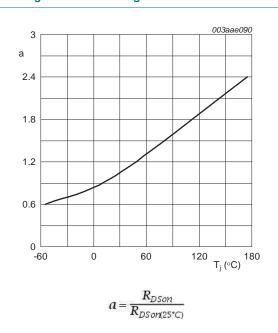


Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature

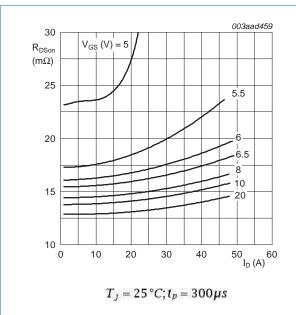


Fig 13. Drain-source on-state resistance as a function of drain current; typical values

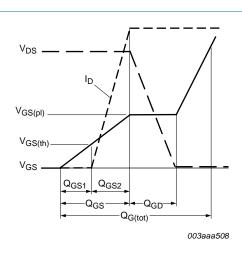


Fig 14. Gate charge waveform definitions

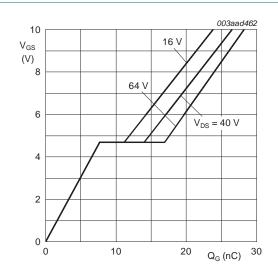


Fig 15. Gate-source voltage as a function of gate charge; typical values

 $T_j=25\,^{\circ}C; I_D=25A$ 

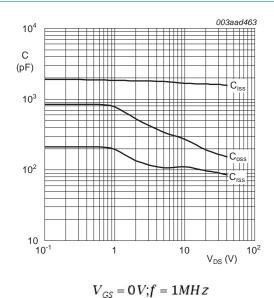
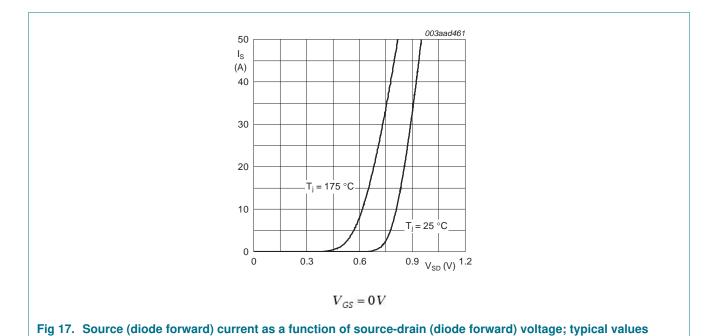
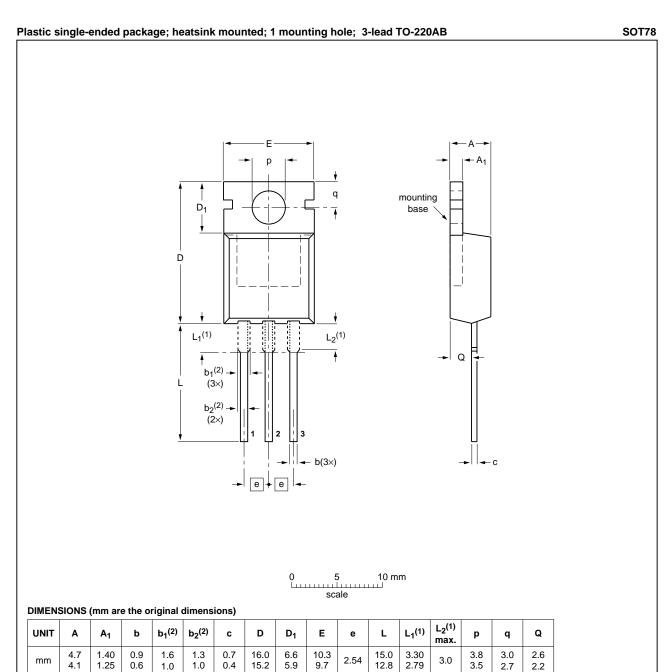


Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



## Package outline



- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT78		3-lead TO-220AB	SC-46		<del>08-04-23</del> 08-06-13

Fig 18. Package outline SOT78 (TO-220AB)

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## 8. Revision history

## Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN017-80PS v.3	20110927	Product data sheet	-	PSMN017-80PS v.2
Modifications:	<ul> <li>Various change</li> </ul>	s to content.		
PSMN017-80PS v.2	20101101	Product data sheet	-	PSMN017-80PS v.1

## 9. Legal information

#### 9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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# **PSMN017-80PS**

## **Nexperia**

N-channel 80 V 17 mΩ standard level MOSFET in TO220

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